

Traceable characterisation of thin film samples for advanced materials by reference-free X-ray fluorescence spectrometry

Motivation

- a growing demand on well-characterized samples in the production and analytical processes [1]
- increasing field of application of thin film layers, e.g. in biotechnology, semi-conductor industry, or in the field of energy conversion and storage
- physically traceable method enabling the quantitative analysis of the mass deposition or mole fraction of the elements in a sample

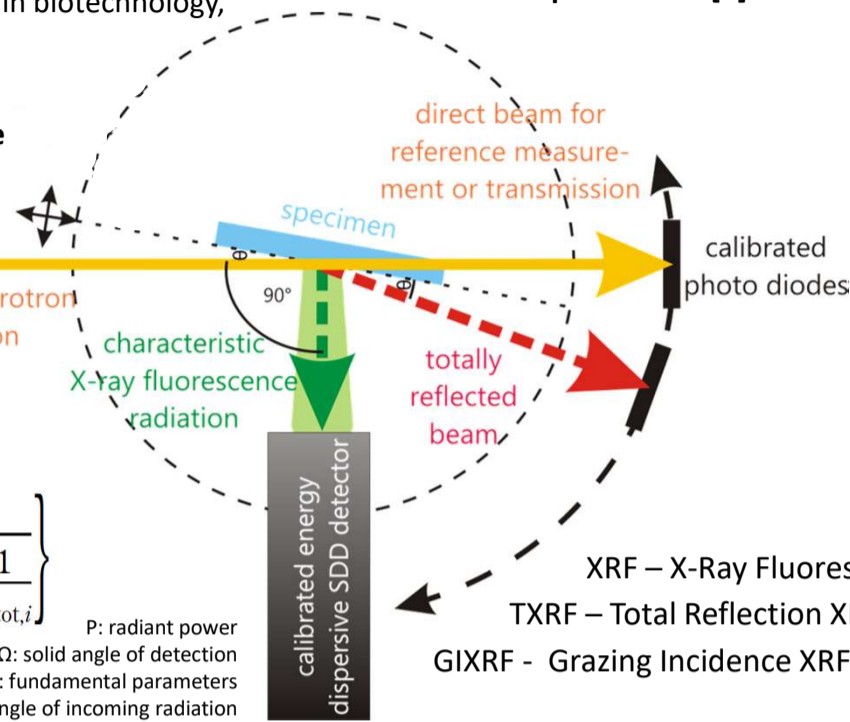
Mass deposition of an element determined by the radiant power of characteristic fluorescence line:

$$\frac{m_i}{F_I} = \frac{-1}{\mu_{tot,i}} \ln \left\{ 1 - \frac{P_i}{P_{0,Wsurf} \tau_{i,E_0} Q \frac{\Omega_{det}}{4\pi} \frac{1}{\sin \psi_{in}} \frac{1}{\mu_{tot,i}}} \right\}$$

P: radiant power
 Ω : solid angle of detection
 μ, τ, Q : fundamental parameters
 ψ : Incident angle of incoming radiation

Reference-free X-ray Spectrometry

- based on well-known synchrotron radiation and radiometrically calibrated instrumentation as well as on the knowledge of the atomic fundamental parameters [2]

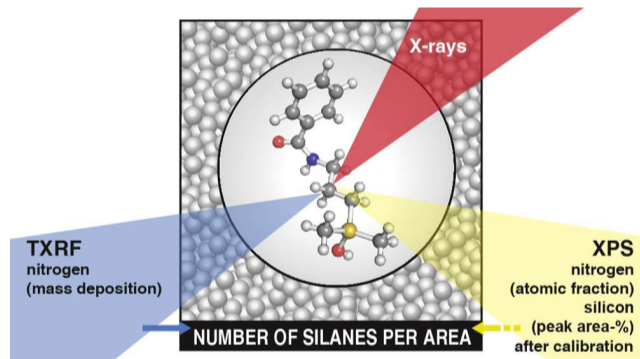


PTB capabilities:

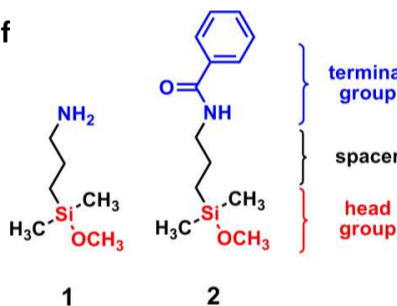
- characterized synchrotron radiation beamlines (well-known spectral distribution, radiant power)
- calibrated photodiodes and calibrated diaphragms
- calibrated detectors with known absolute detection efficiency and response functions
- fundamental atomic parameters determination and databases

Traceable Quantification of Silane Molecules [5]

- traceable and absolute determination of the molecular area density of organic mono-layer of silane molecules by reference-free TXRF
- silanes routinely used to functionalize various support materials to modify surface properties
- hardly reliable quantitative information about surface functional group densities after layer formation available

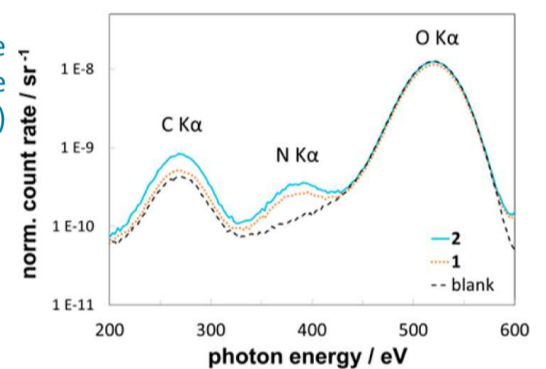


Amino- (1) and Benzamidosilane (2) used for monolayer formation on silicon wafers

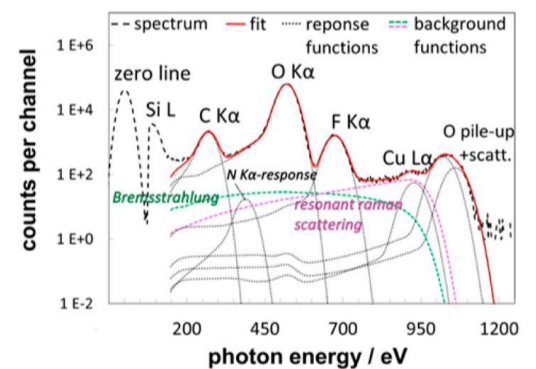


- areic density of 2-4 silane molecules per nm²
- determined from the nitrogen mass deposition obtained by reference-free TXRF
- traceable calibration of X-Ray Photoelectron Spectroscopy: same result by using component intensity of the silane's silicon atom

TXRF spectra of silane layers 1, 2 and the SiO₂/Si wafer (blank)

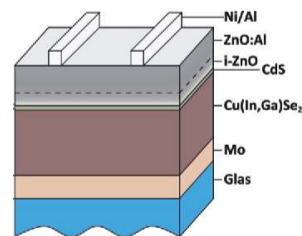
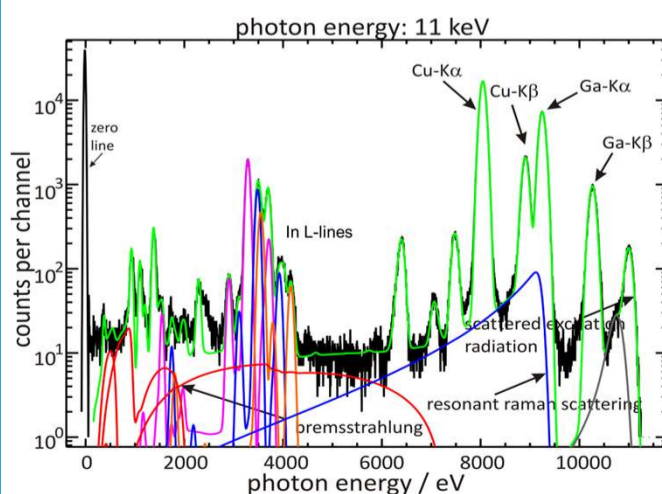


spectral deconvolution based on detector response functions and physical background modeling.



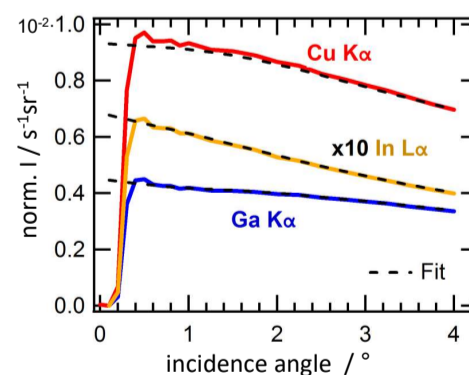
Reference-free quantification of in-depth matrix gradients in CIGS solar cell absorbers [3]

- development of highly efficient thin film solar cells of Cu(In,Ga)Se₂ (CIGS) involves band gap engineering by tuning the elemental in-depth composition
- reference-free GIXRF analysis for a non-destructive analysis of compositional depth profiles in the thin films

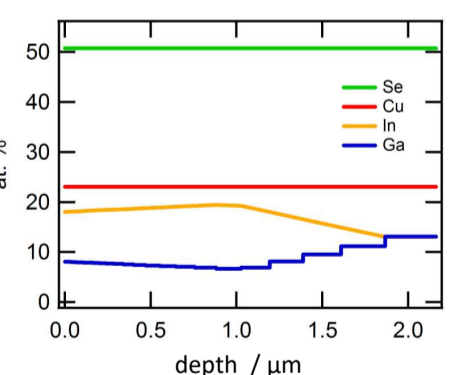


- the variation of the incident angle provides quantitative access to the in-depth distribution
- double Ga gradients can be revealed
- reference-free XRF under conventional 45° conditions had been used for the CCQM-SAWG key comparison K-129 on the measurement of mole fractions of Cu, In, Ga and Se in CIGS [4]

De-convolution with detector response functions, partially in multiplets, and with modeled background contributions



Measured and fitted intensities.



Elemental depth gradient.

| | Cu / at.% | In / at.% | Ga / at.% | Se / at.% | d, x _M / μm |
|----------|------------|---------------------------------|-----------------------------------|------------|------------------------|
| Average | 23.1 ± 1.4 | 17.9 ± 1.9 | 8.3 ± 0.4 | 50.7 ± 2.8 | 2.16 ± 0.08 |
| Gradient | | 18; 19.3; 13 ± 2.0; 2.1; 2.3 | 8.2; 6.9; 13.2 ± 0.9; 1.0; 1.3 | | 1.0 ± 0.2 |

References

- [1] Streeck, et al. Spectroscopy Europe, Vol. 30 No. 1, (2018).
- [2] Beckhoff, JAAS **23**, 845 (2008)
- [3] Streeck et al., Appl. Phys. Lett. **103**, 113904 (2013)
- [4] Kim, et al. Metrologia, Vol. 53(1A), 08011 (2016).
- [5] Dietrich et al., Anal. Chem. **87**, 10117 (2015)

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